

## **NCE N-Channel Super Trench II Power MOSFET**

#### **Description**

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### **Application**

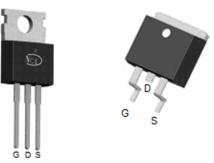
- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

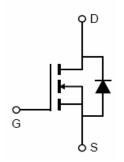
#### **General Features**

- $V_{DS}$  =85V, $I_D$  =95A  $R_{DS(ON)}$ =5.4m $\Omega$  , typical (TO-220)@  $V_{GS}$ =10V  $R_{DS(ON)}$ =5.2m $\Omega$  , typical (TO-263)@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!







**Schematic Diagram** 

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP058N85	NCEP058N85	TO-220	-	-	-
NCEP058N85D	NCEP058N85D	TO-263	-	-	-

#### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	85	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	95	А
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	70	Α
Pulsed Drain Current	I <sub>DM</sub>	380	Α
Maximum Power Dissipation	P <sub>D</sub>	125	W
Derating factor		0.83	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	599	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$ C



# NCEP058N85, NCEP058N85D

## **Thermal Characteristic**

Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

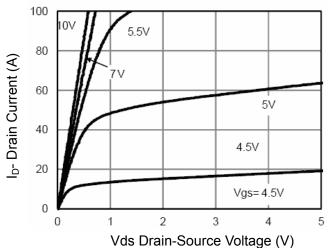
Parameter	Symbol	Ol Condition		Min	Тур	Max	Unit
Off Characteristics				•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA		85		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =85V,V <sub>GS</sub> =0V		-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V		-	-	±100	nA
On Characteristics (Note 3)					l.		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=2$	250μA	2.0	3.0	4.0	V
Danier Courses Our Otata Basistana	-	V <sub>GS</sub> =10V, I <sub>D</sub> =45A	TO-220	-	5.4	5.8	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>		TO-263		5.2	5.8	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =45A			60	-	S
Dynamic Characteristics (Note4)					l.		
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V, F=1.0MHz		-	3550	-	PF
Output Capacitance	Coss			-	540	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	22	-	PF
Switching Characteristics (Note 4)				.N	l.		
Turn-on Delay Time	t <sub>d(on)</sub>			-	14.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =40V, $I_{D}$ =45A $V_{GS}$ =10V, $R_{G}$ =1.6Ω		-	12	-	nS
Turn-Off Delay Time	$t_{d(off)}$			-	35	-	nS
Turn-Off Fall Time	t <sub>f</sub>			-	13	-	nS
Total Gate Charge	Qg	\/ -40\/.	450	-	67	-	nC
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =40V,I <sub>D</sub> =45A, V <sub>GS</sub> =10V		-	20		nC
Gate-Drain Charge	$Q_{gd}$			-	20		nC
Drain-Source Diode Characteristics						•	
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =45A		-		1.2	V
Diode Forward Current (Note 2)	Is			-	-	95	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>		-	66	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>		-	140	-	nC

#### Notes:

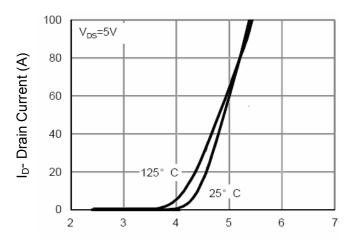
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=40V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$



### **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

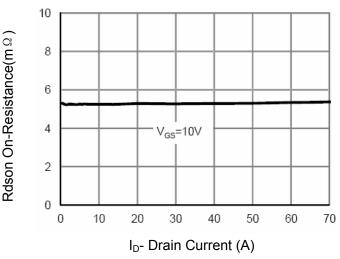
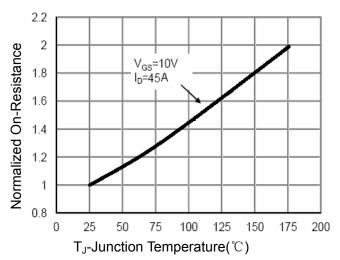


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

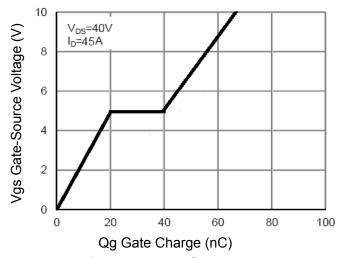


Figure 5 Gate Charge

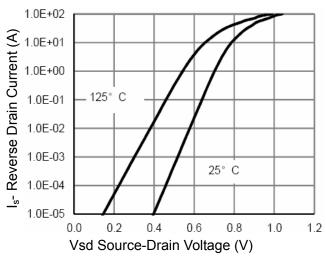


Figure 6 Source- Drain Diode Forward



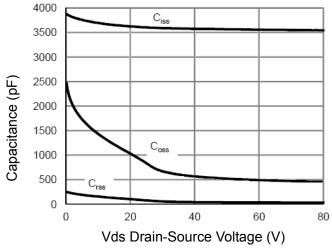


Figure 7 Capacitance vs Vds

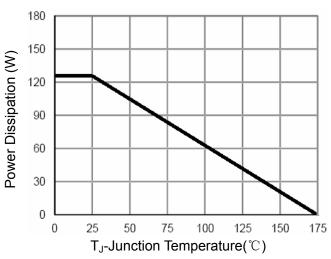
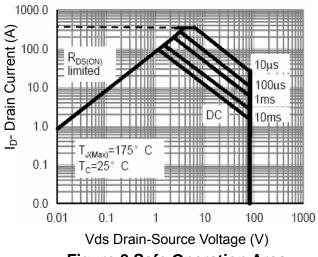


Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

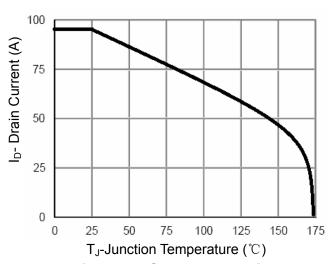


Figure 10 Current De-rating

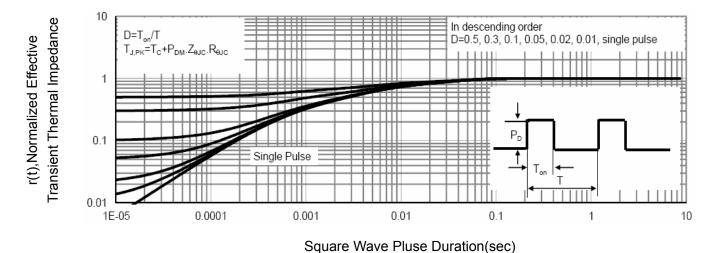
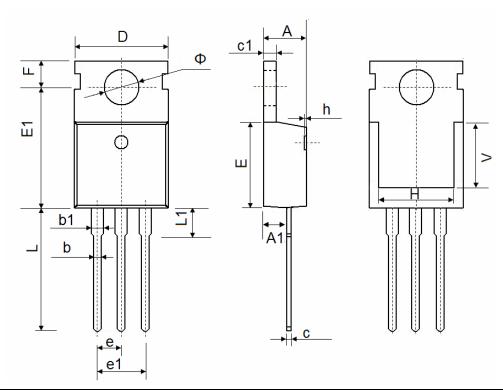


Figure 11 Normalized Maximum Transient Thermal Impedance



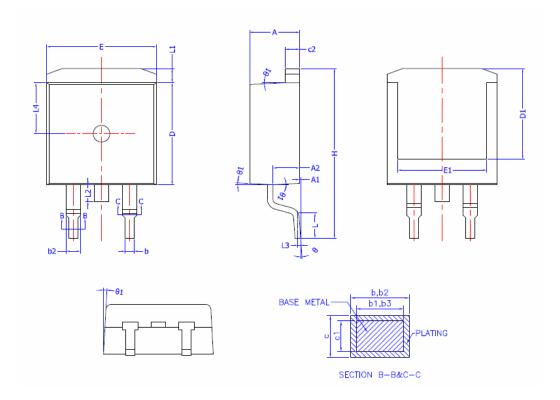
## **TO-220-3L Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.54	0 TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



## **TO-263-2L Package Information**



COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2,20	2,40	2,60	
b	0,76	_	0,89	
b1	0,75	0,80	0,85	
b2	1,23	_	1,37	
b3	1,22	1,27	1,32	
С	0,47	_	0,60	
c1	0.46	0,51	0.56	
c2	1,25	1.30	1,35	
D	9.10	9,20	9.30	
D1	8.00	_	_	
E	9.80	9.90	10.00	
E1	7.80	_	_	
е	2.54 BSC			
Н	14.90	15.30	15.70	
L	2.00	2,30	2.60	
L1 L2	1.17	1.27	1.40	
L2	_	_	1,75	
L3	0.25BSC			
L4	4.60 REF			
θ	0°	_	8°	
θ1	1°	3°	5°	

# NCEP058N85, NCEP058N85D



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